Notice: This is not a final specification. Some parametric limits are subject to change.

Renesas LSIs

M6MGB/T64BS8BWG

67,108,864-BIT (4,194,304-WORD BY 16-BIT) CMOS FLASH MEMORY & 8.388.608-BIT (524,288-WORD BY 16-BIT) CMOS SRAM

Stacked-CSP (Chip Scale Package)

Description

The RENESAS M6MGB/T64BS8BWG is a Stacked Chip Scale Package (S-CSP) that contents 64M-bit Flash memory and 8M-bit SRAM in a 67-pin Stacked CSP for lead free use.

64M-bit Flash memory is a 4,194,304 words, single power supply and high performance non-volatile memory fabricated by CMOS technology for the peripheral circuit and DINOR IV (Divided bit-line NOR IV) architecture for the memory cell. All memory blocks are locked and can not be programmed or erased, when F-WP# is Low. Using Software Lock Release function, program or erase operation can be executed.

8M-bit SRAM is a 524,288 words asynchronous SRAM fabricated by CMOS technology for the peripheral circuit and TFT type transistor for the memory cell.

The RENESAS M6MGB/T64BS8BWG is suitable for a high performance cellular phone and a mobile PC that are required to be small mounting area, weight and small power dissipation.

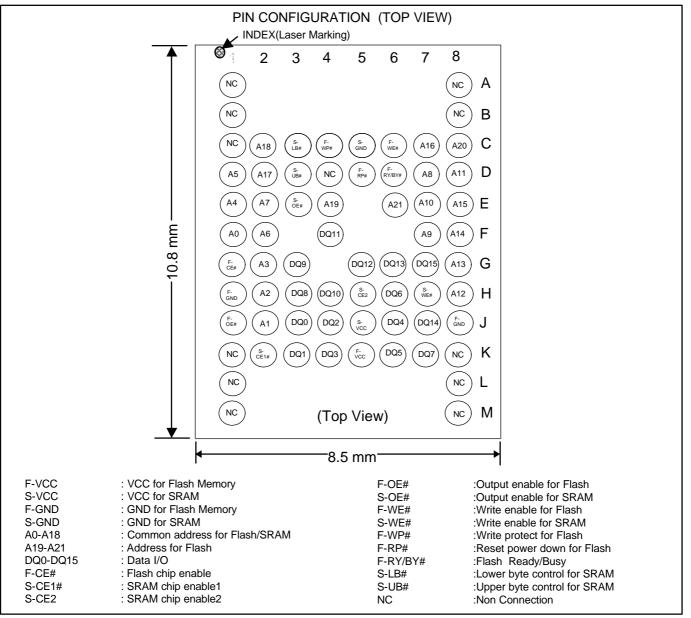
Features

Access Time	Flash
	SRAM
Supply Voltage	
Ambient Tempe	erature
Package	

70ns (Max.) 85ns (Max.) F-VCC =S-VCC=2.7 ~ 3.0V Ta= -40 ~ 85 degree 67pin S-CSP, Ball pitch 0.80mm Outer-ball:Su-Ag-Cu

Application

Mobile communication products





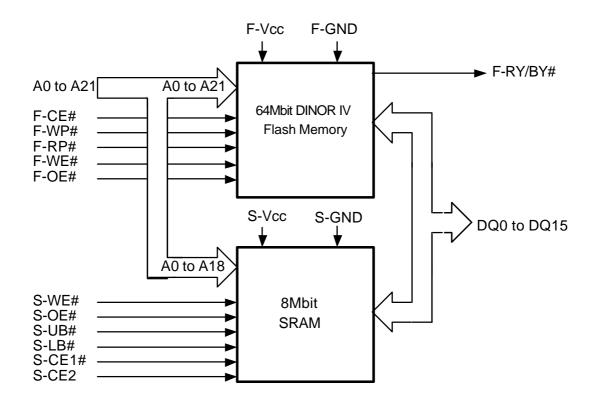
Preliminary

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MCP Block Diagram



Note: In the Flash memory part there are "Vcc", "GND", "OE#" and "WE#" which mean "F-Vcc", "F-GND", "F-OE#" and "F-WE#", respectively. In the SRAM part there are "GND", "UB#", "LB#", "OE#" and "WE#" which mean "S-GND", "S-UB#", "S-LB#", "S-OE#" and "S-WE#", respectively.

Capacitance

Symbol	Parameter	Conditions	Limits			Unit	
			Min.	Тур.	Max.	Onit	
CIN	Input capacitance	A21-A0, F-OE#, F-WE#, F-CE#, F-WP#, F- RP#, S-CE1#, S-CE2, S-OE#, S-WE#, S- LB#, S-UB#	Ta=25°C, f=1MHz, Vin=Vout=0V			18	pF
COUT	Output Capacitance	DQ15-DQ0, F-RY/BY#				22	pF





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Stacked-CSP (Chip Scale Package)

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